

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

Claims 1-10 (Cancelled)

Claim 11. (Currently Amended) A method of fabricating a thin film transistor substrate, comprising:

forming a gate electrode on a substrate;

forming a gate pad and a data pad, at least one of the gate pad and the data pad having a pad hole therein;

forming a gate insulation layer on the gate electrode and on the substrate;

forming an active layer on the gate insulation layer;

forming source and drain electrodes on the active layer to form a thin film transistor, the source and drain electrodes being spaced apart from each other and located over the gate electrode, wherein the drain electrode has a first side facing the source electrode and a second side facing said first side;

forming a protection layer on the thin film transistor and on the gate insulation layer, wherein forming the protection layer includes etching the protection layer to cover the first side but not the second side of the drain electrode, and wherein the protection layer includes a contact hole exposing the pad hole; and

forming a pixel electrode having a plurality of regions wherein a first region is separated from the protection layer at an interval and a second region directly on the gate insulation layer, wherein the second region electrically contacts the second side of the drain electrode, wherein the pixel electrode is formed using a back exposure.

Claim 12. (Original) A method of fabricating a thin film transistor substrate according to claim 11, wherein the pixel electrode is formed overlapping the second side.

Claim 13. (Original) A method of fabricating a thin film transistor substrate according to claim 11, wherein the pixel electrode is formed of a transparent conductive material.

Claim 14. (Original) A method of fabricating a thin film transistor substrate according to claim 13, wherein the transparent conductive material is selected from a group consisting of indium-tin-oxide (ITO) and indium-zinc-oxide (IZO).

Claim 15. (Cancelled)

Claim 16. (Currently Amended) A method of fabricating a thin film transistor substrate according to claim 11, further including:

forming a gate line on the substrate, wherein the gate line includes the gate pad, and wherein the gate line is formed in electrical contact with the gate electrode;

covering the gate pad with the gate insulation layer and the protection layer;

forming the contact hole through the gate insulation layer and through the protection layer to expose at least part of the gate pad; and

forming a gate pad electrode that electrically contacts the gate pad through the contact hole.

Claim 17. (Previously Presented) A method of fabricating a thin film transistor substrate according to claim 16, wherein the pad hole of the gate pad is formed with a substantially bent shape.

Claim 18. (Original) A method of fabricating a thin film transistor substrate according to claim 16, wherein the gate pad electrode is formed on the substrate.

Claim 19. (Currently Amended) A method of fabricating a thin film transistor substrate according to claim 11, further including:

forming a data line on the gate insulation layer, wherein the data line includes the data pad, and wherein the data line is formed in electrical contact with the source electrode;

covering the data pad with the protection layer;

forming [[a]] the contact hole through the protection layer to expose at least part of the data pad; and

forming a data pad electrode that electrically contacts the data pad through the contact hole.

Claim 20. (Previously Presented) A method of fabricating a thin film transistor substrate according to claim 19, wherein the pad hole of the data pad is formed with a substantially bent shape.

Claim 21. (Original) A method of fabricating a thin film transistor substrate according to claim 19, wherein the data pad electrode is formed on the gate insulation layer.

Claims 22-33 (Cancelled)